8-input multiplexer; 3-state Rev. 3 — 9 July 2013

Product data sheet

General description 1.

The 74HC251; 74HCT251 is an 8-bit multiplexer with eight binary inputs (I0 to I7), three select inputs (S0 to S2) and an output enable input (OE). The select inputs select one of the eight binary inputs and route it to the complementary outputs (Y and Y). A HIGH on OE causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. **Features and benefits**

- Input levels:
 - For 74HC251: CMOS level
 - For 74HCT251: TTL level
- Low-power dissipation
- Non-inverting data path
- Specified in compliance with JEDEC standard no. 7A
- ESD protection:
 - HBM JESD22-A114F exceeds 2 000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

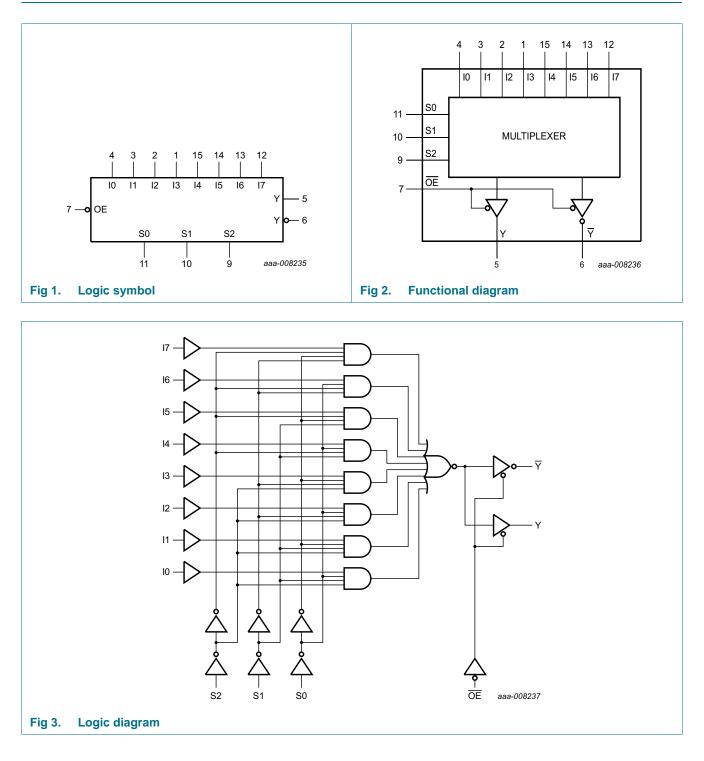
Ordering information 3.

Type number	Package	Package									
	Temperature range	Name	Description	Version							
74HC251N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4							
74HCT251N											
74HC251D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width	SOT109-1							
74HCT251D			3.9 mm								
74HC251DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1							
74HCT251DB			body width 5.3 mm								
74HC251PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads;	SOT403-1							
74HCT251PW			body width 4.4 mm								



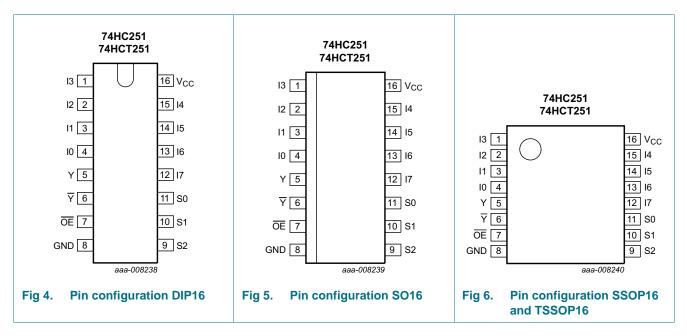
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4. Functional diagram



Pinning information 5.

5.1 Pinning



5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
10 to 17	4, 3, 2, 1, 15, 14, 13, 12	data inputs
Y	5	multiplexer output
Y	6	complementary multiplexer output
OE	7	output enable input (active LOW)
GND	8	ground (0 V)
S0, S1, S2	11, 10, 9	common data select inputs
V _{CC}	16	supply voltage

6. Functional description

Table	3.	Function	table ^[1]
	•••		

Input												Outp	ut
OE	S2	S1	S0	10	11	12	13	14	15	16	17	Y	Y
Н	Х	Х	Х	Х	Х	Х	Х	х	Х	Х	Х	Z	Z
L	L	L	L	L	Х	Х	Х	Х	Х	Х	Х	Н	L
L	L	L	L	Н	Х	Х	Х	Х	Х	Х	Х	L	Н
L	L	L	Н	Х	L	Х	Х	Х	Х	Х	Х	Н	L
L	L	L	Н	Х	Н	Х	Х	Х	Х	Х	Х	L	Н
L	L	Н	L	Х	Х	L	Х	Х	Х	Х	Х	Н	L
L	L	Н	L	Х	Х	Н	Х	Х	Х	Х	Х	L	Н
L	L	Н	Н	Х	Х	Х	L	Х	Х	Х	Х	Н	L
L	L	Н	Н	Х	Х	Х	Н	Х	Х	Х	Х	L	Н
L	Н	L	L	Х	Х	Х	Х	L	Х	Х	Х	Н	L
L	Н	L	L	Х	Х	Х	Х	Н	Х	Х	Х	L	Н
L	Н	L	Н	Х	Х	Х	Х	Х	L	Х	Х	Н	L
L	Н	L	Н	Х	Х	Х	Х	Х	Н	Х	Х	L	Н
L	Н	Н	L	Х	Х	Х	Х	Х	Х	L	Х	Н	L
L	Н	Н	L	Х	Х	Х	Х	Х	Х	Н	Х	L	Н
L	Н	Н	Н	Х	Х	Х	Х	Х	Х	Х	L	Н	L
L	Н	Н	Н	Х	Х	Х	Х	Х	Х	Х	Н	L	Н

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				.0	,
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{\rm I}$ < –0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
Ι _Ο	output current	V_{O} = -0.5 V to (V _{CC} + 0.5 V)	-	±25	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C

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Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$			
	DIP16 package		<u>[1]</u> _	750	mW
	SO16 package		[2] _	500	mW
	(T)SSOP16 package		<u>[3]</u> _	500	mW

[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 $^\circ C.$

[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 $^\circ C.$

[3] For SSOP16 and TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 $^\circ$ C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions		74HC251	l	7	4HCT25	1	Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Ta	_{mb} = 25	°C		-40 °C to 5 °C		-40 °C to 5 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC25 [,]	1					1	1			
V _{IH}	HIGH-level	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	-	1.8	V
√ _{он}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V
		I_{O} = -20 μ A; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_{O} = -5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
/ _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = 20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_{O} = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
1	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±0.1	-	±1.0	-	±1.0	μA
oz	OFF-state output current		-	-	±0.5	-	±5.0	-	±10.0	μA
СС	supply current		-	-	8.0	-	80	-	160	μA
Cı	input capacitance		-	3.5	-					pF

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Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Ta	_{mb} = 25	°C		40 °C to 5 °C	T _{amb} = - +12	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74HCT2	51						1			
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1 0.4	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_O = 0$ A	-	-	±0.5	-	±5.0	-	±10	μA
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	μΑ
∆l _{CC}	additional supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} - 2.1 \text{ V};\\ \text{other inputs at } V_{CC} \text{ or GND};\\ V_{CC} = 4.5 \text{ V to 5.5 V};\\ I_{O} = 0 \text{ A} \end{array}$								
		per input pin; In inputs	-	100	360	-	450	-	490	μΑ
		per input pin; OE input	-	150	540	-	675	-	735	μΑ
		per input pin; Sn input	-	150	540	-	675	-	735	μΑ
CI	input capacitance		-	3.5	-					pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 10.

Symbol	Parameter	Conditions		Tan	_{nb} = 25	°C		= –40 °C ⋅85 °C		-40 °C 25 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HC25	51										
t _{pd}	propagation	In to Y; see Figure 7	<u>[1]</u>								
	delay	$V_{CC} = 2.0 V$		-	50	170	-	215	-	255	ns
		$V_{CC} = 4.5 V$		-	18	34	-	43	-	51	ns
		$V_{CC} = 5 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	15	-	-	-	-	-	ns
		$V_{CC} = 6.0 V$		-	14	29	-	37	-	43	ns
		In to \overline{Y} ; see Figure 7	[1]								
		$V_{CC} = 2.0 V$		-	55	175	-	220	-	265	ns
		$V_{CC} = 4.5 V$		-	20	35	-	44	-	53	ns
		$V_{CC} = 5 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	17	-	-	-	-	-	ns
		$V_{CC} = 6.0 V$		-	16	30	-	37	-	45	ns
		Sn to Y; see Figure 8	[1]								
		$V_{CC} = 2.0 V$		-	66	205	-	255	-	310	ns
		$V_{CC} = 4.5 V$		-	24	41	-	51	-	62	ns
		V _{CC} = 5 V; C _L = 15 pF		-	20	-	-	-	-	-	ns
		$V_{CC} = 6.0 V$		-	19	35	-	43	-	53	ns
		Sn to \overline{Y} ; see Figure 8	[1]								
		$V_{CC} = 2.0 V$		-	69	205	-	255	-	310	ns
		$V_{CC} = 4.5 V$		-	25	41	-	51	-	62	ns
		V _{CC} = 5 V; C _L = 15 pF		-	21	-	-	-	-	-	ns
		$V_{CC} = 6.0 V$		-	20	35	-	43	-	53	ns
t _{en}	enable time	\overline{OE} to Y, \overline{Y} ; see Figure 8	[2]								
		$V_{CC} = 2.0 V$		-	36	140	-	175	-	210	ns
		V _{CC} = 4.5 V		-	13	28	-	35	-	42	ns
		$V_{CC} = 6.0 V$		-	10	24	-	30	-	36	ns
t _{dis}	disable time	\overline{OE} to Y, \overline{Y} ; see Figure 8	[3]								
		V _{CC} = 2.0 V		-	39	140	-	170	-	210	ns
		V _{CC} = 4.5 V		-	14	28	-	35	-	42	ns
		$V_{CC} = 6.0 V$		-	11	24	-	30	-	36	ns
t _t	transition	Y, \overline{Y} ; see Figure 7	[4]								
	time	$V_{CC} = 2.0 V$		-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V		-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V		-	6	13	-	16	-	19	ns
C _{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}; \text{ f} = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[5]</u>	-	44	-	-	-	-	-	pF

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Symbol	Parameter	Conditions		T _{an}	_{nb} = 25	°C		= –40 °C 85 °C		-40 ℃ 25 ℃	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HCT2	51										
t _{pd}	propagation	In to Y; see Figure 7	<u>[1]</u>								
	delay	$V_{CC} = 4.5 V$		-	22	35	-	44	-	53	ns
		$V_{CC} = 5 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	19	-	-	-	-	-	ns
		In to \overline{Y} ; see Figure 7	<u>[1]</u>								
		$V_{CC} = 4.5 V$		-	22	35	-	44	-	53	ns
		$V_{CC} = 5 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	19	-	-	-	-	-	ns
		Sn to Y; see Figure 8	[1]								
		$V_{CC} = 4.5 V$		-	24	44	-	55	-	66	ns
		$V_{CC} = 5 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	20	-	-	-	-	-	ns
		Sn to \overline{Y} ; see Figure 8	<u>[1]</u>								
		V _{CC} = 4.5 V		-	25	44	-	55	-	66	ns
		V _{CC} = 5 V; C _L = 15 pF		-	21	-	-	-	-	-	ns
t _{en}	enable time	\overline{OE} to Y, \overline{Y} ; see Figure 8	[2]								
		V _{CC} = 4.5 V		-	13	28	-	35	-	42	ns
		V _{CC} = 5 V; C _L = 15 pF		-	13	-	-	-	-	-	ns
t _{dis}	disable time	\overline{OE} to Y, \overline{Y} ; see Figure 8	[3]								
		V _{CC} = 4.5 V		-	14	28	-	35	-	42	ns
		V _{CC} = 5 V; C _L = 15 pF		-	18	-	-	-	-	-	ns
t _t	transition	Y, \overline{Y} ; see Figure 7	[4]								
	time	V _{CC} = 4.5 V		-	7	15	-	19	-	22	ns
C _{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[5]	-	46	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 10.

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] t_{en} is the same as t_{PZH} and t_{PZL} .

- [3] t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [4] t_t is the same as t_{THL} and t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W). $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where: $f_i =$ input frequency in MHz; $f_o =$ output frequency in MHz;

 C_L = output load capacitance in pF;

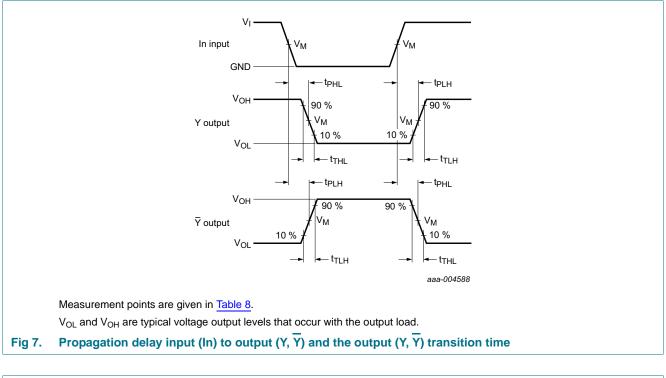
 V_{CC} = supply voltage in V;

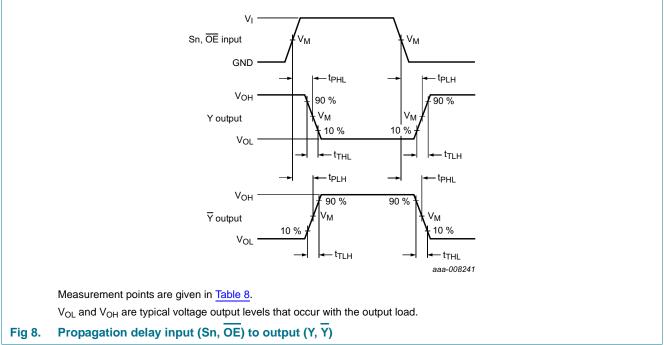
N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of outputs.

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11. Waveforms





NXP Semiconductors

74HC251; 74HCT251

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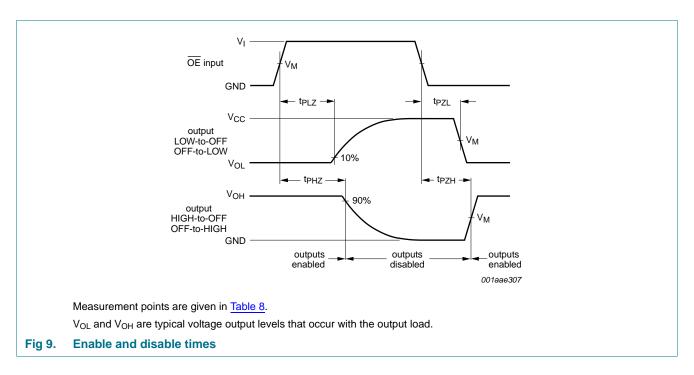


Table 8. Measurement points

Туре	Input	Output	
	V _M	V _M	
74HC251	0.5V _{CC}	0.5V _{CC}	
74HCT251	1.3 V	1.3 V	

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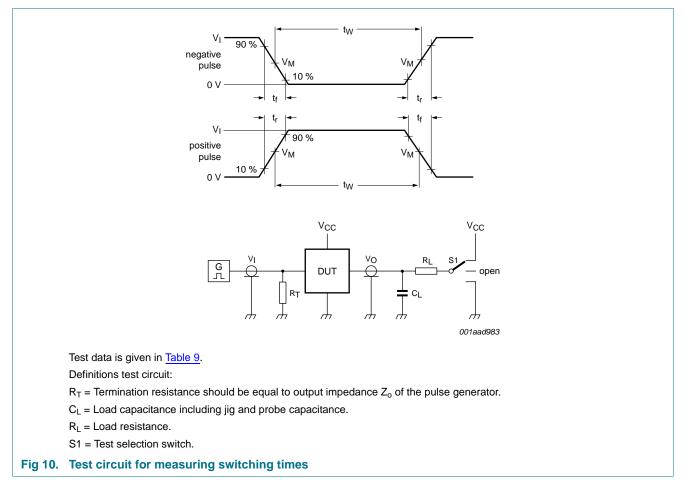


Table 9. Test data

Туре	Input		Load		S1 position		
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
74HC251	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}
74HCT251	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}

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12. Package outline

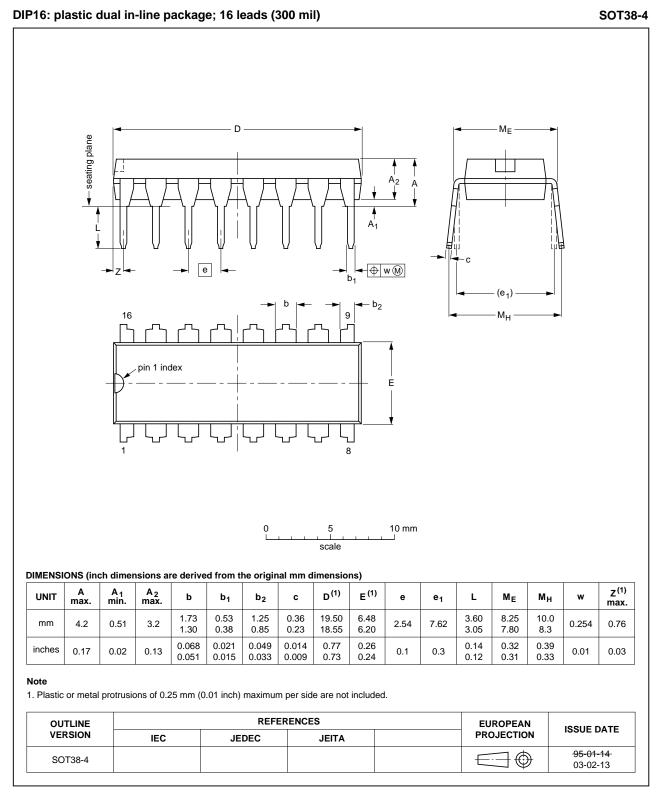


Fig 11. Package outline SOT38-4 (DIP16)

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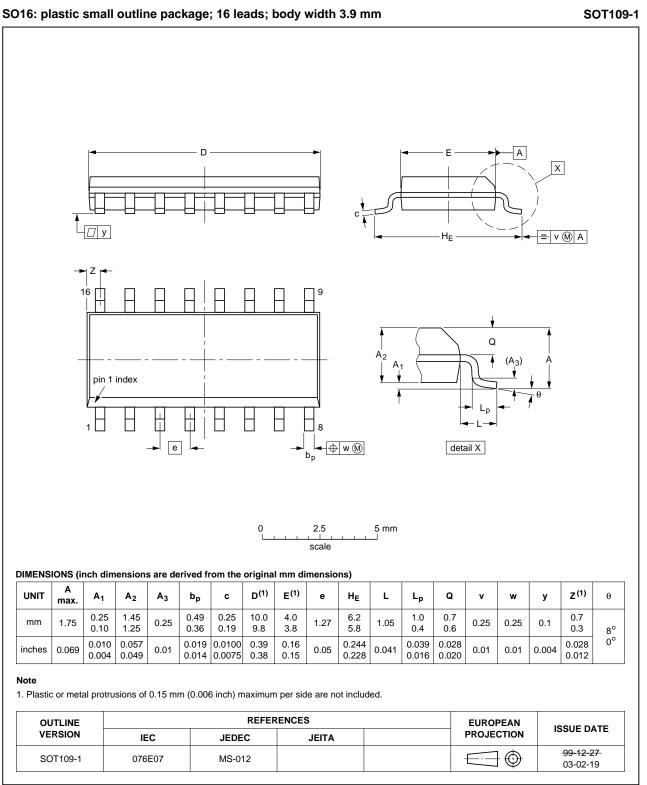


Fig 12. Package outline SOT109-1 (SO16)

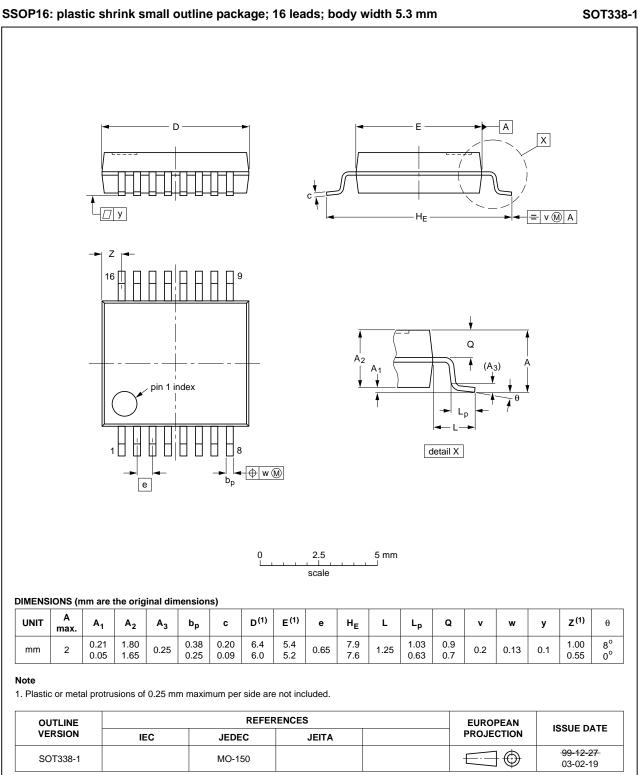


Fig 13. Package outline SOT338-1 (SSOP16)

8-input multiplexer; 3-state

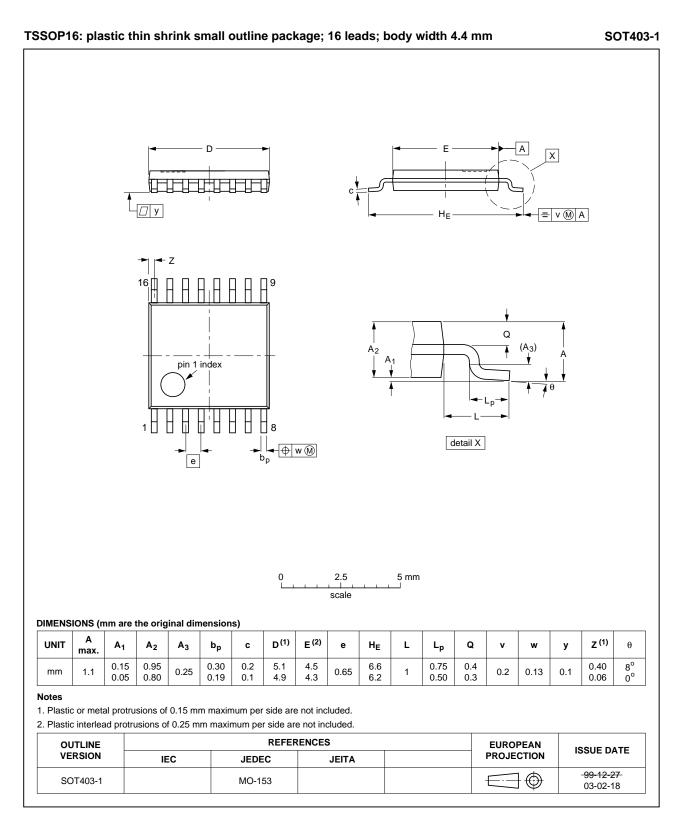


Fig 14. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

AcronymDescriptionCMOSComplementary Metal Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelTTLTransistor-Transistor Logic	Table 10.	Abbreviations		
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelTTLTransistor-Transistor Logic	Acronym	Description		
ESD ElectroStatic Discharge HBM Human Body Model MM Machine Model TTL Transistor-Transistor Logic	CMOS	Complementary Metal Oxide Semiconductor		
HBM Human Body Model MM Machine Model TTL Transistor-Transistor Logic	DUT	Device Under Test		
MM Machine Model TTL Transistor-Transistor Logic	ESD	ElectroStatic Discharge		
TTL Transistor-Transistor Logic	HBM	Human Body Model		
	MM	Machine Model		
KATL KAPPA	TTL	Transistor-Transistor Logic		
MIL Military	MIL	Military		

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT251 v.3	20130709	Product data sheet	-	74HC_HCT251_CNV v.2
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 			
	 Legal texts 	have been adapted to th	e new company name	e where appropriate.
74HC_HCT251_CNV v.2	19970828	Product specification	-	

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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8-input multiplexer; 3-state

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